

**Amendments to the Claims:**

This listing of Claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-10 (canceled)

Claim 11 (currently amended):

A non-volatile memory structure, including:

a base;

a gate dielectric layer on the base, wherein the gate dielectric layer has an increased electron trapping density and has at least one kind of hereto element comprising compound of Oxygen (O), other than Nitrogen;

a gate electrode layer on the top of the said gate dielectric layer; and

a source/drain electrodes at the base on both sides of the said gate dielectric layer.

Claim 12 (previously presented):

The non-volatile memory structure as claimed in claim 11, where the gate dielectric layer in turns from bottom to the top including a first oxide layer, a nitride layer and a second oxide layer.

Claims 13-16 (canceled)